Jamie D Phillips

List of Publications by Year
in descending order

176 papers	4,840 citations	101384 36 h-index	114278 63 g-index
180 all docs	180 docs citations	180 times ranked	4011 citing authors

#	Article	IF	Citations
1	Evaluation of the fundamental properties of quantum dot infrared detectors. Journal of Applied Physics, 2002, 91, 4590-4594.	1.1	246
2	Far-infrared photoconductivity in self-organized InAs quantum dots. Applied Physics Letters, 1998, 72, 2020-2022.	1.5	229
3	Room-temperature operation of In0.4Ga0.6As/GaAs self-organised quantum dot lasers. Electronics Letters, 1996, 32, 1374.	0.5	211
4	Self-assembled InAs-GaAs quantum-dot intersubband detectors. IEEE Journal of Quantum Electronics, 1999, 35, 936-943.	1.0	205
5	Intermediate-band photovoltaic solar cell based on ZnTe:O. Applied Physics Letters, 2009, 95, .	1.5	199
6	Absorption, carrier lifetime, and gain in inas~gaas quantum-dot infrared photodetectors. IEEE Journal of Quantum Electronics, 2003, 39, 459-467.	1.0	145
7	Sub-bandgap photoconductivity in ZnO epilayers and extraction of trap density spectra. Semiconductor Science and Technology, 2006, 21, 717-723.	1.0	133
8	Mid-wave infrared HgCdTe nBn photodetector. Applied Physics Letters, 2012, 100, .	1.5	114
9	Drift-Diffusion Modeling for Impurity Photovoltaic Devices. IEEE Transactions on Electron Devices, 2009, 56, 3168-3174.	1.6	99
10	ZnO thin-film transistors with polycrystalline (Ba,Sr)TiO3 gate insulators. Applied Physics Letters, 2006, 88, 212903.	1.5	98
11	Optimization of random diffraction gratings in thin-film solar cells using genetic algorithms. Solar Energy Materials and Solar Cells, 2008, 92, 1689-1696.	3.0	98
12	In(Ga)As/GaAs self-organized quantum dot lasers: DC and small-signal modulation properties. IEEE Transactions on Electron Devices, 1999, 46, 871-883.	1.6	95
13	AlGaAs Photovoltaics for Indoor Energy Harvesting in mm-Scale Wireless Sensor Nodes. IEEE Transactions on Electron Devices, 2015, 62, 2170-2175.	1.6	87
14	Small-signal modulation and differential gain of single-mode self-organized In0.4Ga0.6As/GaAs quantum dot lasers. Applied Physics Letters, 1997, 70, 2952-2953.	1.5	86
15	Trap-related photoconductivity in ZnO epilayers. Journal of Electronic Materials, 2006, 35, 543-549.	1.0	85
16	Photoluminescence and far-infrared absorption in Si-doped self-organized InAs quantum dots. Applied Physics Letters, 1997, 71, 2079-2081.	1.5	79
17	Self-organized In0.4Ga0.6As quantum-dot lasers grown on Si substrates. Applied Physics Letters, 1999, 74, 1355-1357.	1.5	79
18	A New Class of Roomâ€Temperature Multiferroic Thin Films with Bismuthâ€Based Supercell Structure. Advanced Materials, 2013, 25, 1028-1032.	11.1	78

#	Article	IF	Citations
19	Nanometer-scale studies of vertical organization and evolution of stacked self-assembled InAs/GaAs quantum dots. Applied Physics Letters, 1999, 74, 2824-2826.	1.5	71
20	Model for intermediate band solar cells incorporating carrier transport and recombination. Journal of Applied Physics, 2009, 105, 064512.	1.1	69
21	Design and Modeling of HgCdTe nBn Detectors. Journal of Electronic Materials, 2011, 40, 1624-1629.	1.0	65
22	Subcutaneous Photovoltaic Infrared Energy Harvesting for Bio-implantable Devices. IEEE Transactions on Electron Devices, 2017, 64, 2432-2437.	1.6	65
23	Interdiffusion and surface segregation in stacked self-assembled InAs/GaAs quantum dots. Applied Physics Letters, 1999, 75, 2797-2799.	1.5	58
24	A DC Voltage Dependant Switchable Thin Film Bulk Wave Acoustic Resonator Using Ferroelectric Thin Film. IEEE MTT-S International Microwave Symposium Digest IEEE MTT-S International Microwave Symposium, 2007, , .	0.0	55
25	Gain dynamics and ultrafast spectral hole burning in In(Ga)As self-organized quantum dots. Applied Physics Letters, 2002, 81, 670-672.	1.5	51
26	Growth and structural properties of m-plane ZnO on MgO (001) by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 233505.	1.5	51
27	Generation and recombination rates at ZnTe:O intermediate band states. Applied Physics Letters, 2009, 95, .	1.5	51
28	Energy Harvesting for GaAs Photovoltaics Under Low-Flux Indoor Lighting Conditions. IEEE Transactions on Electron Devices, 2016, 63, 2820-2825.	1.6	49
29	Hysteretic metalâ€“ferroelectricâ€“ semiconductor capacitors based on PZT/ZnO heterostructures. Journal Physics D: Applied Physics, 2007, 40, 2430-2434.	1.3	45
30	Optical Characteristics of ZnTeO Thin Films Synthesized by Pulsed Laser Deposition and Molecular Beam Epitaxy. Journal of Electronic Materials, 2009, 38, 119-125.	1.0	44
31	Design of an Auger-Suppressed Unipolar HgCdTe NBÎ½N Photodetector. Journal of Electronic Materials, 2012, 41, 2886-2892.	1.0	44
32	Detailed study of above bandgap optical absorption in HgCdTe. Journal of Electronic Materials, 2005, 34, 773-778.	1.0	43
33	Thermal emission in type-II GaSb/GaAs quantum dots and prospects for intermediate band solar energy conversion. Journal of Applied Physics, 2012, 111, 074514.	1.1	43
34	Characteristics of InAs/AlGaAs self-organized quantum dot modulation doped field effect transistors. Applied Physics Letters, 1998, 72, 3509-3511.	1.5	37
35	Linear and quadratic electro-optic coefficients of self-organized In0.4Ga0.6As/GaAs quantum dots. Applied Physics Letters, 1998, 72, 1275-1277.	1.5	37
36	Predicted Performance Improvement of Auger-Suppressed HgCdTe Photodiodes and $phbox{-}n$ Heterojunction Detectors. IEEE Transactions on Electron Devices, 2011, 58, 501-507.	1.6	37

#	Article	IF	Citations
37	Bistability and self-pulsation in quantum-dot lasers with intracavity quantum-dot saturable absorbers. Applied Physics Letters, 1999, 74, 1654-1656.	1.5	36
38	Normal incidence narrowband transmission filtering capabilities using symmetry-protected modes of a subwavelength, dielectric grating. Optics Letters, 2015, 40, 2637.	1.7	36
39	An Intrinsically Switchable FBAR Filter Based on Barium Titanate Thin Films. IEEE Microwave and Wireless Components Letters, 2009, 19, 359-361.	2.0	33
40	Improving Linearity of Ferroelectric-Based Microwave Tunable Circuits. IEEE Transactions on Microwave Theory and Techniques, 2007, 55, 354-360.	2.9	32
41	Intrinsically switchable, high-Q ferroelectric-on-silicon composite film bulk acoustic resonators. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2014, 61, 231-238.	1.7	32
42	Multiphoton Sub-Band-Gap Photoconductivity and Critical Transition Temperature in Type-II GaSb Quantum-Dot Intermediate-Band Solar Cells. Physical Review Applied, 2014, 1, .	1.5	32
43	21.4 A >78%-efficient light harvester over 100-to-100klux with reconfigurable PV-cell network and MPPT circuit. , 2016, 2016, 370-371.		32
44	Analysis of the intermediate-band absorption properties of type-II GaSb/GaAs quantum-dot photovoltaics. Physical Review B, 2017, 96, .	1.1	32
45	Bias-controlled wavelength switching in coupled-cavity In0.4Ga0.6As/GaAs self-organized quantum dot lasers. Applied Physics Letters, 1999, 74, 783-785.	1.5	31
46	MWIR and LWIR HgCdTe Infrared Detectors Operated with Reduced Cooling Requirements. Journal of Electronic Materials, 2010, 39, 873-881.	1.0	31
47	Electronic properties of ferroelectric BaTiO3âˆ•MgO capacitors on GaAs. Applied Physics Letters, 2004, 85, 3208-3210.	1.5	30
48	26.9 A 0.19Ã—0.17mm‹sup›2‹/sup› Wireless Neural Recording IC for Motor Prediction with Near-Infrared-Based Power and Data Telemetry. , 2020, 2020, 416-418.		29
49	Threading and misfit-dislocation motion in molecular-beam epitaxy-grown HgCdTe epilayers. Journal of Electronic Materials, 2003, 32, 710-716.	1.0	28
50	Modeling of LWIR HgCdTe Auger-Suppressed Infrared Photodiodes under Nonequilibrium Operation. Journal of Electronic Materials, 2008, 37, 1362-1368.	1.0	28
51	Modeling and Design Considerations of HgCdTe Infrared Photodiodes under Nonequilibrium Operation. Journal of Electronic Materials, 2007, 36, 846-851.	1.0	26
52	The disintegration of GaSb/GaAs nanostructures upon capping. Applied Physics Letters, 2013, 102, .	1.5	26
53	Carrier dynamics in self-organized quantum dots and their application to long-wavelength sources and detectors. Journal of Crystal Growth, 2001, 227-228, 27-35.	0.7	25
54	ZnO/ZnSe/ZnTe Heterojunctions for ZnTe-Based Solar Cells. Journal of Electronic Materials, 2011, 40, 1674-1678.	1.0	24

#	Article	IF	Citations
55	Room temperature strong coupling effects from single ZnO nanowire microcavity. Optics Express, 2012, 20, 11830.	1.7	24
56	Room temperature luminescence from self-organized quantum dots with high size uniformity. Journal of Crystal Growth, 1997, 175-176, 720-724.	0.7	23
57	A Linearity Improvement Technique for Thin-film Barium Strontium Titanate Capacitors. , 2006, , .		23
58	Bridging the â€œLast Millimeterâ€•Gap of Brain-Machine Interfaces via Near-Infrared Wireless Power Transfer and Data Communications. ACS Photonics, 2021, 8, 1430-1438.	3.2	23
59	Properties of electrical contacts on bulk and epitaxial n-type ZnO. Journal of Electronic Materials, 2005, 34, 389-394.	1.0	22
60	Free carrier absorption and lattice vibrational modes in bulk ZnO. Journal of Electronic Materials, 2006, 35, 525-529.	1.0	22
61	Memristors Based on (Zr, Hf, Nb, Ta, Mo, W) Highâ€Entropy Oxides. Advanced Electronic Materials, 2021, 7, 2001258.	2.6	22
62	Electrical Characteristics and Photoresponse of ZnO/ZnTe Heterojunction Diodes. Journal of Electronic Materials, 2008, 37, 1044-1048.	1.0	21
63	Complementary Thin-Film Electronics Based on n-Channel ZnO and p-Channel ZnTe. IEEE Electron Device Letters, 2009, 30, 1314-1316.	2.2	21
64	Three-Bandgap Absolute Quantum Efficiency in GaSb/GaAs Quantum Dot Intermediate Band Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 508-512.	1.5	21
65	Ternary Alloy Rare-Earth Scandate as Dielectric for eta -Ga₂O₃ MOS Structures. IEEE Transactions on Electron Devices, 2019, 66, 2489-2495.	1.6	21
66	Pressure-induced energy level crossings and narrowing of photoluminescence linewidth in self-assembled InAlAs/AlGaAs quantum dots. Applied Physics Letters, 1999, 74, 1549-1551.	1.5	20
67	Optical-absorption model for molecular-beam epitaxy HgCdTe and application to infrared detector photoresponse. Journal of Electronic Materials, 2004, 33, 701-708.	1.0	20
68	Broadband long-wavelength infrared Si/SiO_2 subwavelength grating reflector. Optics Letters, 2012, 37, 1523.	1.7	20
69	Composition control of long wavelength MBE HgCdTe using In-situ spectroscopic ellipsometry. Journal of Electronic Materials, 2001, 30, 643-646.	1.0	19
70	Control of very-long-wavelength infrared HgCdTe detector-cutoff wavelength. Journal of Electronic Materials, 2002, 31, 664-668.	1.0	19
71	Optical absorption properties of HgCdTe epilayers with uniform composition. Journal of Electronic Materials, 2003, 32, 646-650.	1.0	19
72	Uniformity of optical absorption in HgCdTe epilayer measured by infrared spectromicroscopy. Applied Physics Letters, 2003, 83, 3701-3703.	1.5	19

#	Article	IF	Citations
73	Energy Harvesting in Nanosystems: Powering the Next Generation of the Internet of Things. Frontiers in Nanotechnology, 2021, 3, .	2.4	19
74	A Light-Tolerant Wireless Neural Recording IC for Motor Prediction With Near-Infrared-Based Power and Data Telemetry. IEEE Journal of Solid-State Circuits, 2022, 57, 1061-1074.	3.5	19
75	Growth of HgCdTe for long-wavelength infrared detectors using automated control from spectroscopic ellipsometry measurements. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1580.	1.6	18
76	Small-Area Si Photovoltaics for Low-Flux Infrared Energy Harvesting. IEEE Transactions on Electron Devices, 2017, 64, 15-20.	1.6	18
77	Highâ€efficiency photovoltaic modules on a chip for millimeterâ€scale energy harvesting. Progress in Photovoltaics: Research and Applications, 2019, 27, 540-546.	4.4	17
78	Growth of InSb on GaAs using InAlSb buffer layers. Journal of Crystal Growth, 2000, 209, 567-571.	0.7	16
79	Polarization-independent narrowband transmittance filters via symmetry-protected modes in high contrast gratings. Optics Letters, 2020, 45, 4348.	1.7	16
80	Parameter extraction of HgCdTe infrared photodiodes exhibiting Auger suppression. Journal Physics D: Applied Physics, 2009, 42, 234003.	1.3	15
81	Far-infrared modulated photoluminescence spectroscopy of InSb/GaSb quantum dot structures. Physical Review B, 2003, 68, .	1.1	14
82	Growth and electronic properties of ZnO epilayers by plasma-assisted molecular beam epitaxy. Journal of Electronic Materials, 2005, 34, 699-703.	1.0	14
83	Lateral indiumâ€“indium pair correlations within the wetting layers of buried InAs/GaAs quantum dots. Applied Physics Letters, 2002, 81, 1423-1425.	1.5	13
84	Pulsed laser annealing of self-organized InAs/GaAs quantum dots. Journal of Electronic Materials, 2004, 33, L5-L8.	1.0	13
85	Properties of ferroelectric Pb(Zr,Ti)O3 thin films on ZnO/Al2O3 (0001) epilayers. Thin Solid Films, 2005, 491, 301-304.	0.8	13
86	Analysis and design optimization of electrooptic interferometric modulators for microphotonics applications. Journal of Lightwave Technology, 2006, 24, 2340-2346.	2.7	13
87	Electric field dependence of piezoelectric coefficient in ferroelectric thin films. Journal of Electroceramics, 2006, 17, 613-617.	0.8	13
88	Bias-Temperature-Stress Characteristics of $ hbox{ZnO/HfO}_{2}$ Thin-Film Transistors. IEEE Transactions on Electron Devices, 2012, 59, 1488-1493.	1.6	13
89	Advances in large-area Hg1â^'xCdxTe photovoltaic detectors for remote-sensing applications. Journal of Electronic Materials, 2002, 31, 726-731.	1.0	12
90	Infrared Energy Harvesting in Millimeter-Scale GaAs Photovoltaics. IEEE Transactions on Electron Devices, 2017, 64, 4554-4560.	1.6	12

#	Article	IF	Citations
91	Long-wavelength infrared transmission filters via two-step subwavelength dielectric gratings. Optics Letters, 2017, 42, 518.	1.7	12
92	Low damage electrical modification of 4H-SiC via ultrafast laser irradiation. Journal of Applied Physics, 2018, 123, .	1.1	12
93	Surface morphology and straight crack generation of ultrafast laser irradiated Î²-Ga2O3. Journal of Applied Physics, 2019, 125, 223104.	1.1	12
94	Intersubband absorption and photoluminescence in Si-doped self-organized InAs/Ga(Al)As quantum dots. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1343.	1.6	11
95	Nanodot formation induced by femtosecond laser irradiation. Applied Physics Letters, 2014, 105, .	1.5	11
96	Demonstration of a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>G</mml:mtext><mml:mtext>aS</mml:mtext><mml:mtext>b</mml:mtext><mml:mo></mm Quantum Dot Intermediate Band Solar Cell Operating at Maximum Power Point. Physical Review Letters, 2020, 125, 247703.	2.9	11
97	Optical waveguiding in BaTiO3âˆ•MgOâˆ•AlxOyâˆ•GaAs heterostructures. Applied Physics Letters, 2004, 85, 5206-5208.	1.5	10
98	Quantum Confinement and Carrier Localization Effects in ZnO/Mg x Zn1âˆ’x O Wells Synthesized by Pulsed Laser Deposition. Journal of Electronic Materials, 2008, 37, 749-754.	1.0	10
99	Effects of high temperature annealing on the atomic layer deposited HfO2/Î²-Ga2O3(010) interface. Journal of Applied Physics, 2022, 131, .	1.1	10
100	Epitaxial growth and surface modeling of ZnO on c-plane Al2O3. Applied Physics Letters, 2004, 85, 6338-6340.	1.5	9
101	Electrical Characteristics of PEDOT:PSS Organic Contacts to HgCdTe. Journal of Electronic Materials, 2007, 36, 841-845.	1.0	9
102	Arsenic Diffusion Study in HgCdTe for Low p-Type Doping in Auger-Suppressed Photodiodes. Journal of Electronic Materials, 2010, 39, 945-950.	1.0	9
103	Intrinsically switchable thin film ferroelectric resonators. , 2012, , .		9
104	Intermediate Band to Conduction Band Optical Absorption in ZnTeO. IEEE Journal of Photovoltaics, 2014, 4, 1091-1094.	1.5	8
105	Dual color longwave InAs/GaSb type-II strained layer superlattice detectors. Infrared Physics and Technology, 2015, 70, 93-98.	1.3	8
106	A 179-Lux Energy-Autonomous Fully-Encapsulated 17-mm³ Sensor Node with Initial Charge Delay Circuit for Battery Protection. , 2018, , .		8
107	InGaAs/GaAsSb Type-II Superlattices for Short-Wavelength Infrared Detection. Journal of Electronic Materials, 2019, 48, 6025-6029.	1.0	8
108	InAsSb/InPSb strained-layer superlattice growth using metal-organic chemical vapor deposition. Journal of Crystal Growth, 2000, 211, 400-404.	0.7	7

#	Article	IF	Citations
109	Admittance Spectroscopy of Interface States in $ hbox{ZnO/HfO}_{2}$ Thin-Film Electronics. IEEE Electron Device Letters, 2011, 32, 1713-1715.	2.2	7
110	Transport properties of ZnTe:N thin films. Applied Physics Letters, 2013, 103, 042108.	1.5	7
111	A Light Tolerant Neural Recording IC for Near-Infrared-Powered Free Floating Motes. , 2021, 2021, .		7
112	Adatom migration effects during molecular beam epitaxial growth of InGaAs/GaAs quantum wells on patterned substrates with vertical sidewalls: Blue shift in luminescence spectra. Applied Physics Letters, 1996, 68, 1120-1122.	1.5	6
113	Self-organized growth of In(Ga)As/GaAs quantum dots and their opto-electronic device applications. Bulletin of Materials Science, 1999, 22, 519-529.	0.8	6
114	Intrinsically switchable contour mode acoustic wave resonators based on barium titanate thin films. , 2009, , .		6
115	Intermediate-band solar cells based on dilute alloys and quantum dots. Frontiers of Optoelectronics in China, 2011, 4, 2-11.	0.2	6
116	A DC voltage dependent switchable acoustically coupled BAW filter based on BST-on-silicon composite structure. , 2012, , .		6
117	Intrinsically Switchable Ferroelectric Contour Mode Resonators. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 2806-2813.	2.9	6
118	Investigating Student Motivation and Performance in Electrical Engineering and Its Subdisciplines. IEEE Transactions on Education, 2016, 59, 241-247.	2.0	6
119	Chemical epitaxy and interfacial reactivity in solution deposited PbS on ZnTe. Journal of Materials Chemistry C, 2016, 4, 1996-2002.	2.7	6
120	Dual-Junction GaAs Photovoltaics for Low Irradiance Wireless Power Transfer in Submillimeter-Scale Sensor Nodes. IEEE Journal of Photovoltaics, 2020, 10, 1721-1726.	1.5	6
121	A low-power communication scheme for wireless, 1000 channel brainâ€“machine interfaces. Journal of Neural Engineering, 2022, 19, 036037.	1.8	6
122	Temperature-dependent photoluminescence of In0.5Al0.5As/Al0.25Ga0.75As self-organized quantum dots. Journal of Applied Physics, 1999, 85, 2997-2999.	1.1	5
123	A ferroelectric-based impedance tuner for adaptive matching applications. , 2008, , .		5
124	Illumination instabilities in ZnO/HfO2 thin-film transistors and influence of grain boundary charge. Journal of Materials Research, 2012, 27, 2199-2204.	1.2	5
125	Preserving voltage and long wavelength photoresponse in GaSb/GaAs quantum dot solar cells. , 2013, , .		5
126	Distinguishing Optical Behavior of Oxygen States and Native Deep Level Emission in ZnTe. Journal of Electronic Materials, 2014, 43, 879-883.	1.0	5

#	Article	IF	Citations
127	Oxygen Incorporation in ZnTeO Alloys via Molecular Beam Epitaxy. Journal of Electronic Materials, 2014, 43, 889-893.	1.0	5
128	Resolving spectral overlap issue of intermediate band solar cells using nonâ€uniform subâ€bandgap state filling. Progress in Photovoltaics: Research and Applications, 2014, 22, 1062-1069.	4.4	5
129	Heterojunction Band Offset Limitations on Open-Circuit Voltage in <roman>p</roman>-Z<roman>n</roman>T <roman>e/n</roman>-Z<roman>n</roman>S<roman>e</roman> Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 874-877.	1.5	5
130	Charge trapping and recovery in ALD HfO₂/Î²-Ga₂O₃ (010) MOS capacitors. Semiconductor Science and Technology, 2021, 36, 04LT01.	1.0	5
131	Large blueshift in the photoluminescence of pseudomorphic InGaAs/GaAs quantum wells grown in patterned (100) GaAs grooves and ridges with vertical sidewalls. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2312.	1.6	4
132	Thermoradiative Cell Equivalent Circuit Model. IEEE Transactions on Electron Devices, 2021, 68, 928-930.	1.6	4
133	mSAIL. , 2021, , .		4
134	Conduction band offsets in CdZnSSe/ZnSSe single quantum wells measured by deep level transient spectroscopy. Applied Physics Letters, 1996, 68, 3591-3593.	1.5	3
135	Growth and electroluminescent properties of self-organized In[sub 0.4]Ga[sub 0.6]As/GaAs quantum dots grown on silicon. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1116.	1.6	3
136	Exploring new active regions for type I InAsSb strained-layer lasers. Journal of Electronic Materials, 2000, 29, 91-93.	1.0	3
137	Quantum dot carrier dynamics and far-infrared devices. , 2000, 4078, 84.		3
138	Passivation of long-wave infrared InAs/GaSb superlattice detectors with epitaxially grown ZnTe. , 2014, , .		3
139	Indoor photovoltaic energy harvesting for mm-scale systems. , 2014, , .		3
140	The effect of doping on low temperature growth of high quality GaAs nanowires on polycrystalline films. Nanotechnology, 2016, 27, 495605.	1.3	3
141	Influence of Subwavelength Grating Asymmetry on Long-Wavelength Infrared Transmittance Filters. IEEE Photonics Journal, 2018, 10, 1-8.	1.0	3
142	Mid-wave infrared transmittance filters in suspended GaAs subwavelength gratings. Applied Physics Letters, 2021, 119, 031103.	1.5	3
143	Mid-wave infrared filtering in silicon subwavelength zero-contrast gratings. , 2020, , .		3
144	Electron intersubband energy level spacing in self-organized In[sub 0.4]Ga[sub 0.6]As/GaAs quantum dot lasers from temperature-dependent modulation measurements. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1276.	1.6	2

#	Article	IF	Citations
145	In(Ga)As/GaAs self-organized quantum dot light emitters grown on silicon substrates. Journal of Crystal Growth, 1999, 201-202, 1186-1189.	0.7	2
146	Decoupling spectral overlap of intermediate band solar cells using low-high state filling. , 2012, , .		2
147	Intermediate band solar energy conversion in ZnTeO. , 2013, , .		2
148	Epitaxial growth of ZnTe on GaSb(100) using in situ ZnCl2 surface clean. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 03C118.	0.6	2
149	Variable-Field Hall Effect Analysis of HgCdTe Epilayers with Very Low Doping Density. Journal of Electronic Materials, 2017, 46, 5479-5483.	1.0	2
150	Analysis of Carrier Transport in n-Type Hg1â^'xCdxTe with Ultra-Low Doping Concentration. Journal of Electronic Materials, 2018, 47, 5699-5704.	1.0	2
151	Carrier dynamics of intermediate sub-bandgap transitions in ZnTeO. Journal of Applied Physics, 2019, 126, 135701.	1.1	2
152	Room temperature self-organized quantum dot transistors. , 0, , .		1
153	High-speed quantum well and quantum dot lasers. , 1998, 3547, 350.		1
154	High-speed modulation of quantum-dot lasers. , 1999, , .		1
155	Far infrared modulated photoluminescence in InSb quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 598-602.	1.3	1
156	ZnO nanorods for simultaneous light trapping and transparent electrode application in solar cells. , 2011, , .		1
157	Calculated performance of an Auger-suppressed unipolar HgCdTe photodetector for high temperature operation. , 2011, , .		1
158	Unipolar barrier-integrated HgCdTe infrared detectors. , 2012, , .		1
159	Highly selective GaAs/AlGaAs dry etching using HBr/SF6/He. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2021, 39, 052202.	0.6	1
160	Room temperature operation of MBE self-organized InGaAs quantum dot lasers. , 0, , .		0
161	Room temperature luminescence and 1 Î¼m junction laser operation of In/sub x/Ga/sub 1-x/As/GaAs quantum boxes formed by self-organized molecular beam. , 0, , .		0
162	Strain tensor, electronic spectra and carrier dynamics in In(Ga)As/GaAs self-assembled quantum dots. , 1997, , .		0

#	Article	IF	Citations
163	Growth and properties of self-organized In/sub 0.4/Ga/sub 0.6/As-GaAs quantum dot light emitting diodes on silicon substrates. , 0, , .		0
164	Optoelectronic Device Applications of Self-Organized In(Ga,Al)As/Ga(Al)As Quantum Dots. Materials Research Society Symposia Proceedings, 2000, 618, 195.	0.1	0
165	Deposition Of BaTiO3 Thin Films And MgO Buffer Layers On Patterned GaAs Substrates For Integrated Optics Applications. Materials Research Society Symposia Proceedings, 2003, 784, 11231.	0.1	0
166	Optical absorption studies of HgCdTe epitaxial layers for improved infrared detector modeling. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 662-665.	0.8	0
167	Frontiers in semiconductor-based devices. Journal Physics D: Applied Physics, 2009, 42, 230301-230301.	1.3	0
168	Atomic Resolution TEM Study on Quantum Dots in ZnSe/ZnTe Heterostructure. Microscopy and Microanalysis, 2011, 17, 1646-1647.	0.2	0
169	Room Temperature Polariton Lasing in a Single ZnO Nanowire Microcavity. , 2012, , .		0
170	Suspended Si/air high contrast subwavelength gratings for long-wavelength infrared reflectors. Proceedings of SPIE, 2013, , .	0.8	0
171	Narrowband infrared transmission filters via asymmetric subwavelength dielectric gratings. , 2016, , .		0
172	Leaky mode coupling in asymmetric subwavelength dielectric gratings. , 2017, , .		0
173	Notice of Removal Three-bandgap absolute quantum efficiency in intermediate band solar cells. , 2017, , .		0
174	Influence of Finite Grating Size on Guided Mode Resonance Transmission Filters. , 2018, , .		0
175	A Stacked-Photovoltaic-Cell Energy Harvester with >81% Indoor Light Harvesting Efficiency for Millimeter-Scale Energy-Autonomous Sensor Nodes. , 2021, , .		0
176	Tracking the Migration of the Monarch Butterflies with the World's Smallest Computer. GetMobile (New York, N Y), 2022, 26, 25-29.	0.7	0